

Abstract Submitted
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Emission study on the gamma-ray irradiation effects on the ferroelectric $\text{Pb}(\text{Zr},\text{Ti})\text{O}_3$ thin films YUNSANG LEE, JUNWHI LIM, Soongsil University, SUN A YANG, S. D. BU, Chonbuk National University — We investigated the photoluminescence of the gamma-ray irradiated $\text{Pb}(\text{Zr},\text{Ti})\text{O}_3$ (PZT) thin films with the various total doses up to 1000 kGy. The PZT thin films were prepared on the Pt/Ti/SiO₂/Si substrates by using a sol-gel method with a spin-coating process. It was found that the visible emission emerges near 550 nm with the gamma-ray irradiation. The intensity of the emission increased with the increasing dose amount. The spectral feature of the gamma-ray induced emission was quite narrow, which was distinguished from that formed by normal defects such as oxygen vacancy. We suggest that the gamma-ray irradiation should generate a specific type of defect state inside the PZT films, which could be detected by the low temperature photoluminescence spectroscopy.

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